Attorney's Docket No.: 14580/045001/FP2078

Amendment to the Claims:

This listing of claims replaces all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method for producing a hard mask in a capacitor device comprising the steps of:

applying a photosensitive sol-gel layer to said capacitor device;

applying a pattern to said sol-gel layer to form a patterned layer; and

applying a <u>nitrogen</u> thermal decomposition treatment to said patterned layer to convert it to a hard mask layer comprising a metal nitride.

- 2. (Original) A method according to claim 1, further comprising the step of etching said hard mask layer according to said pattern to provide a pattern for the etching of one or more layers in said capacitor device.
- 3. (Original) A method according to claim 1, wherein the step of applying said photosensitive sol-gel layer comprises applying a titanium organic gel layer.

Attorney's Docket No.: 14580/045001/FP2078

- 4. (Original) A method according to claim 1, wherein the step of applying said photosensitive sol-gel layer comprises applying a titanium-aluminium organic gel layer.
- 5. (Original) A method according to claim 1, wherein the step of applying said photosensitive sol-gel layer comprises applying a mixture of one or more titanium alkoxides with ethyl acetoactate (EacAc).
- 6. (Original) A method according to claim 5, wherein the step of applying said photosensitive sol-gel layer comprises applying a mixture of one or more of (TiOEt)4 or Ti(OEt)4 plus Al(OBu)3 with ethyl acetoactate (EacAc).
- 7. (Original) A method according to claim 1, wherein the step of applying a pattern comprises applying said pattern using a photolithographic process.

8-11. (Canceled)

- 12. (Currently Amended) A method according to claim 11 1, wherein the step of applying a thermal decomposition treatment comprises applying a nitrogen thermal decomposition treatment to convert said patterned layer to a TiN hard mask material.
- 13. (Currently Amended) A method according to claim $\frac{11}{2}$, wherein the step of applying a thermal decomposition treatment

Attorney's Docket No.: 14580/045001/FP2078

comprises applying a nitrogen thermal decomposition treatment to convert said patterned layer to an Al-Ti-N hard mask material.

- 14. (Original) A method according to claim 1, wherein the step of applying said photosensitive organic gel layer comprises applying said layer using a spin coating technique.
- 15. (Original) A ferroelectric capacitor device etched according to the hard mask formed according to the method of claim 1.
- 16. (Original) A FeRAM device etched according to the hard mask formed according to the method of claim 1.
- 17. (Original) A hard mask formed according to the method of claim 1.